

**isc Silicon NPN Power Transistor**

**2SD878**

**DESCRIPTION**

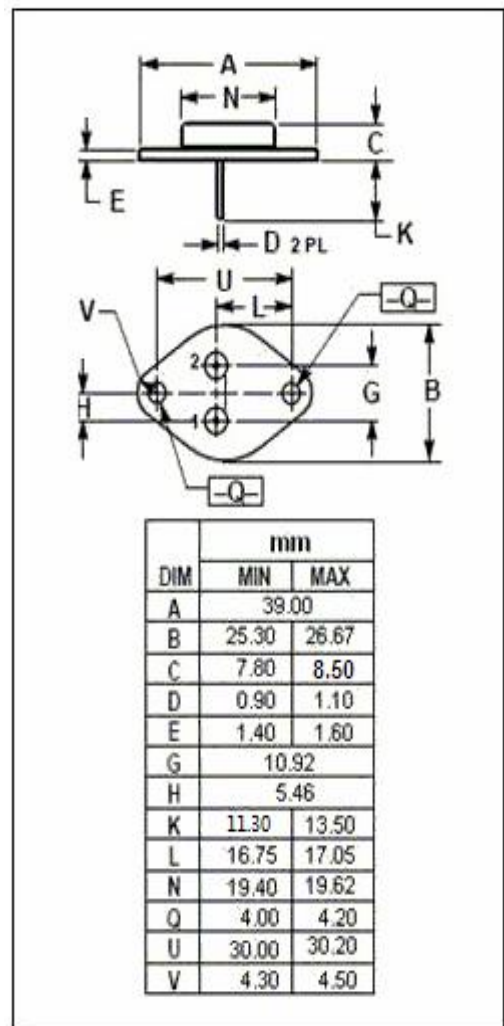
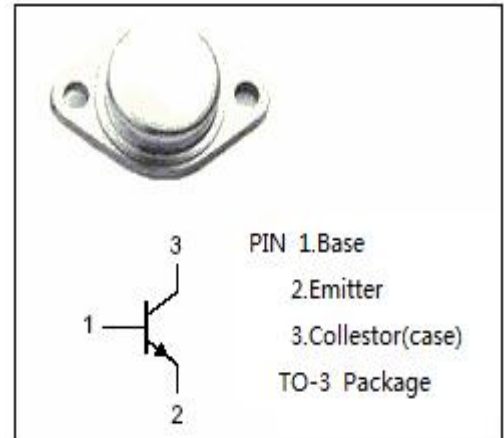
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 60V$  (Min)
- High Power Dissipation
- High Current Capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- High power amplifier applications.
- High power switching applications.
- DC-DC converter applications.
- Regulator applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	MAX	UNIT
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	15	A
$I_B$	Base Current-Continuous	7	A
$P_C$	Collector Power Dissipation @ $T_c = 25^\circ C$	115	W
$T_j$	Junction Temperature	175	$^\circ C$
$T_{stg}$	Storage Temperature Range	-65~175	$^\circ C$



**isc Silicon NPN Power Transistor****2SD878****ELECTRICAL CHARACTERISTICS**T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	60			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.4A		0.3	1.1	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 4A; V <sub>CE</sub> = 4V		1.1	1.8	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 4V	20		70	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 10A; V <sub>CE</sub> = 4V	5			
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		150		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V		1.5		MHz

**Switching Times**

t <sub>on</sub>	Turn-on Time	V <sub>CC</sub> = 50V, R <sub>L</sub> = 10 Ω, I <sub>B1</sub> = I <sub>B2</sub> = 0.5A		2.5		μs
t <sub>stg</sub>	Storage Time			3.5		
t <sub>f</sub>	Fall Time			1.2		

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